



ZXTN2038F SOT23 80 volt NPN silicon planar medium power transistor

Summary

 $V_{(BR)CEV} > 80V$

 $V_{(BR)CEO} > 60V$

 $I_{c(cont)} = 1A$

 $V_{ce(sat)} < 500 mV @ 1A$

Complementary type

ZXTP2039F

Description

This transistor combines high gain, high current operation and low saturation voltage making it ideal for power MOSFET gate driving and low loss power switching.

Features

- · Low saturation voltage for reduced power dissipation
- · 1 to 2 amp high current capability
- · Pb-free
- SOT23 package

Applications

- · Power MOSFET gate driving
- · Low loss power switching

Ordering information

Device Reel size		Tape width	Quantity per reel	
ZXTN2038FTA 7"		8mm	3,000	
ZXTN2038FTC	13"	8mm	10,000	

Device marking

N38

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V _{CBO}	80	V
Collector-emitter voltage	V _{CEV}	80	V
Collector-emitter voltage	V _{CEO}	60	V
Emitter-base voltage	V _{EBO}	5.0	V
Peak pulse current	I _{CM}	2	Α
Continuous collector current (*)	Ic	1	Α
Peak base current	I _{BM}	1	Α
Power dissipation @ T _A =25°C ^(*)	P _D	350	mW
Operating and storage temperature	T _j :T _{stg}	55 to +150	°C

NOTES:

^(*) For a device surface mounted on a 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

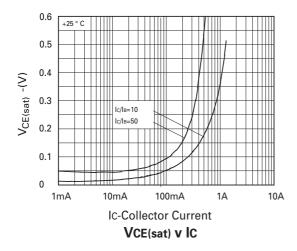
Electrical characteristics (@ $T_{AMB} = 25$ °C)

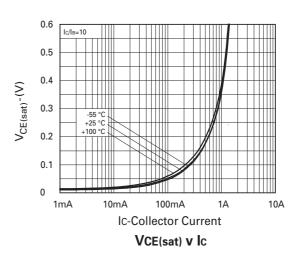
Parameter	Symbol	Min.	Max.	Unit	Conditions
Collector-base breakdown voltage	V _{(BR)CBO}	80		V	I _C =100μA
Collector-emitter breakdown voltage	V _{(BR)CEV}	80		V	$I_{C}=100\mu A,$ $0.3V > V_{BE} > -1V$
Collector-emitter breakdown voltage	V _{(BR)CEO}	60		V	I _C =10mA (*)
Emitter-base breakdown voltage	V _{(BR)EBO}	5		V	I _E =100μA
Collector-emitter cut-off current	I _{CES}		100	nA	V _{CE} =60V
Collector-base cut-off current	I _{CBO}		100	nA	V _{CB} =60V
Emitter-base cut-off current	I _{EBO}		100	nA	V _{EB} =4V
Static forward current transfer ratio	h _{FE}	100 100 80 30	300		I _C =1mA, V _{CE} =5V I _C =500mA, V _{CE} =5V ^(*) I _C =1A, V _{CE} =5V ^(*) I _C =2A, V _{CE} =5V ^(*)
Collector-emitter saturation voltage	V _{CE(sat)}		0.2 0.25 0.5	V V V	I _C =100mA, I _B =2mA ^(*) I _C =500mA, I _B =50mA ^(*) I _C =1A, I _B =100mA ^(*)
Base-emitter saturation voltage	V _{BE(sat)}		1.1	V	I _C =1A, I _B =100mA ^(*)
Base-emitter turn-on voltage	V _{BE(on)}		1.0	V	I _C =1A, V _{CE} =5V ^(*)
Transition frequency	f _T	150			I _C =50mA, V _{CE} =10V f=100MHz
Output capacitance	C _{obo}		10	pF	V _{CB} =10V, f=1MHz

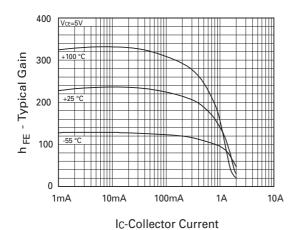
NOTES:

(*) Measured under pulsed conditions. Pulse width=300 μ S. Duty cycle $\le \! 2\%$ Spice parameter data is available upon request for this device

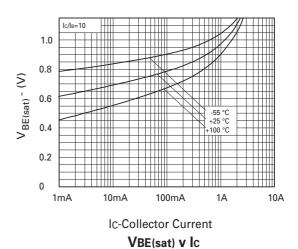
Typical characteristics

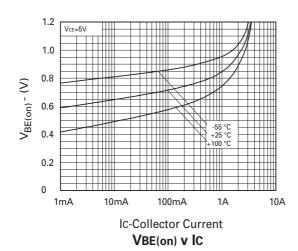


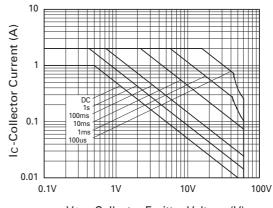




hfe V IC



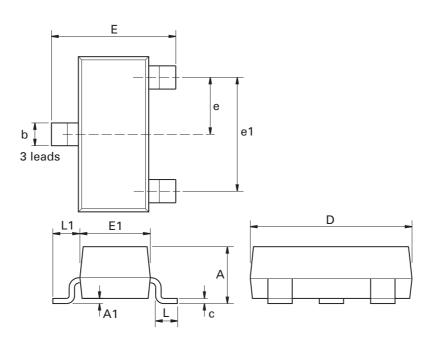




VCE - Collector Emitter Voltage (V)

Safe Operating Area

Packaging details - SOT23



Package dimensions

Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	Е	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	-			-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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